

ASC100N1700MDSK

1700V, 100A, 26mΩ, N-Channel, Silicon Carbide MOSFET

Product Data Sheet

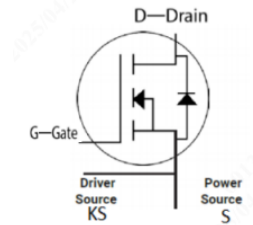
ASTC-3T04-65A A/0



爱仕特科技
AST TECHNOLOGY

General Description

The AST-MDS series SiC MOSFET in SOT-227 package ensures stable high-temperature operation for power-dense and energy-critical systems, enabling compact designs with reduced EMI.



Features

- 3rd Generation SiC MOSFET Technology
- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low $R_{DS(on)}$
- Optimized package with Separate Driver Source Pin
- Easy to parallel and Simple to Drive
- RoHS Compliant, Halogen Free



Applications

- EV Charging
- High Voltage DC/DC Converters
- Switch Mode Power Supplies
- Power Factor Correction Modules

Ordering Informations

Order Number	ASC100N1700MDSK
Marking	ASC100N1700MDSK
Package Type	SOT-227
Packing Method	Box

Key Parameters

Symbol	Parameter	Values			Unit	Test Conditions
Absolute maximum rating						
V _{DS}	Drain-Source Voltage	1700			V	T _C =25°C
I _D	Drain Current (continuous)	100			A	T _C =25°C
P _D	Power Dissipation	600			W	T _C =25°C
T _J	Junction Temperature	-55 to +175			°C	
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
Static characteristics						
R _{DS(on)}	Static Drain-Source on Resistance	-	26	33	mΩ	V _{GS} =18V; I _D =50A; T _J =25°C
Dynamic characteristics						
Q _G	Total Gate Charge	-	168	-	nC	V _{DS} =1200V; V _{GS} =-5V/18V; I _D =50A; T _J =25°C
Q _{GD}	Gate-Drain Charge	-	55	-		
Source-drain diode						
Q _{rr}	Reverse Recovery Charge	-	718	-	nC	V _{GS} =-5V; I _F =50A; V _R =1200V; di/dt=1900A/μs; T _J =175°C

Absolute Maximum Ratings (at $T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Values	Unit
V_{DS}	Drain-Source Voltage	1700	V
I_D	Drain Current (continuous; $T_c=25^\circ\text{C}$)	100	A
	Drain Current (continuous; $T_c=100^\circ\text{C}$)	75	
I_{DM}	Drain Current (pulsed)	200	A
V_{GS}	Gate-Source Voltage	-10/+22	V
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	600	W
T_J, T_{stg}	Junction and Storage Temperature Range	-55 to +175	$^\circ\text{C}$

MOSFET Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
Static characteristics (at T _J =25°C unless otherwise specified)						
BV _{DS}	Drain-Source Breakdown Voltage	1700	-	-	V	I _D =250μA; V _{GS} =0V
I _{DSS}	Zero Gate Voltage Drain Current	-	5	100	μA	V _{DS} =1700V; V _{GS} =0V
I _{GSS}	Gate-Body Leakage Current	-	10	250	nA	V _{DS} =0V; V _{GS} =-10 to 20V
V _{GS(th)}	Gate Threshold Voltage	2	3	4	V	V _{DS} =V _{GS} ; I _D =10mA
V _{GS(on)}	Recommended Turn-on Voltage	-	18	-	V	Static
V _{GS(off)}	Recommended Turn-off Voltage	-	-5	-		
R _{DS(on)}	Static Drain-Source on Resistance	-	26	33	mΩ	V _{GS} =18V; I _D =50A; T _J =25°C
		-	44	-		V _{GS} =18V; I _D =50A; T _J =175°C
Dynamic characteristics (at T _J =25°C unless otherwise specified)						
C _{iss}	Input Capacitance	-	6460	-	pF	V _{DS} =1200V; f=1MHz; V _{AC} =25mV
C _{oss}	Output Capacitance	-	198	-		
C _{rss}	Reverse Transfer Capacitance	-	16	-		
g _{fs}	Transconductance	-	52	-	S	V _{DS} =20V; I _D =50A
E _{oss}	Coss Stored Energy	-	152	-	μJ	V _{DS} =1200V; f=1MHz
E _{on}	Turn-on Energy (Body Diode)	-	2.32	-	mJ	V _{DS} =1200V; V _{GS} =-5/18V; I _D =50A; L=150μH; R _{G(ext)} =2.5Ω; T _J =175°C
E _{off}	Turn-off Energy (Body Diode)	-	0.78	-		
Q _G	Total Gate Charge	-	168	-	nC	V _{DS} =1200V; V _{GS} =-5V/18V; I _D =50A
Q _{GS}	Gate-Source Charge	-	52	-		
Q _{GD}	Gate-Drain Charge	-	55	-		
R _{G(int)}	Internal Gate Resistance	-	2.5	-	Ω	f=1MHz; V _{AC} =25mV
t _{d(on)}	Turn-on Delay Time	-	55	-	ns	V _{DS} =1200V; V _{GS} =-5V/18V; I _D =50A; L=150μH; R _{G(ext)} =2.5Ω
t _r	Rise Time	-	38	-		
t _{d(off)}	Turn-off Delay Time	-	68	-		
t _f	Fall Time	-	23	-		

Body Diode Characteristics (at $T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
V_{SD}	Diode Forward Voltage	-	3.2	6	V	$V_{GS}=0\text{V}$; $I_F=37.5\text{A}$; $T_J=25^{\circ}\text{C}$
		-	2.9	6		$V_{GS}=0\text{V}$; $I_F=37.5\text{A}$; $T_J=175^{\circ}\text{C}$
I_S	Continuous Diode Forward Current	-	100	-	A	$V_{GS}=0\text{V}$; $T_C=25^{\circ}\text{C}$
T_{rr}	Reverse Recovery Time	-	68	-	ns	$V_{GS}=-5\text{V}$; $I_F=50\text{A}$; $V_R=1200\text{V}$; $di/dt=1900\text{A}/\mu\text{s}$; $T_J=175^{\circ}\text{C}$
Q_{rr}	Reverse Recovery Charge	-	718	-	nC	
I_{rm}	Peak Reverse Recovery Current	-	20	-	A	

Thermal Characteristics

Symbol	Parameter	Value.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.25	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	40	$^{\circ}\text{C}/\text{W}$

The values are based on Junction-to-Case Thermal Impedance measured with the device mounted to a large heat sink, assuming a maximum junction temperature of $T_{J(max)}=175^{\circ}\text{C}$.

Typical Performance

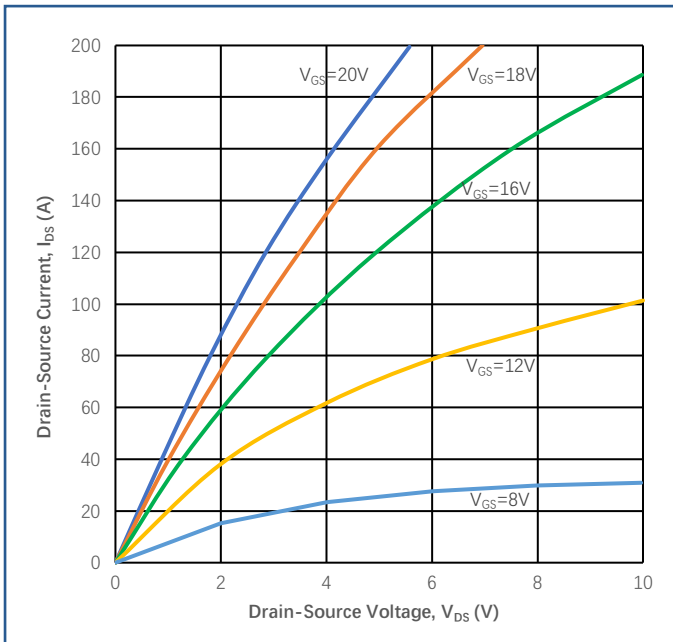


Figure 1
Output Characteristics ($T_J = 25^\circ\text{C}$)

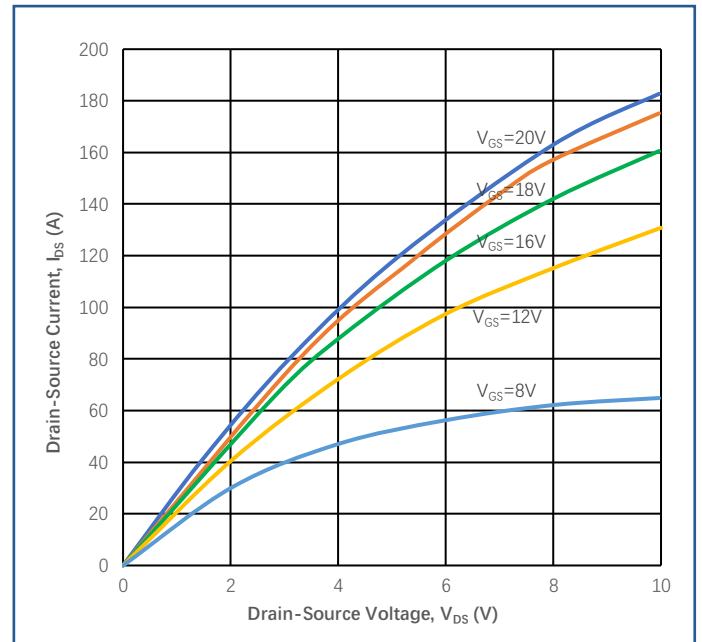


Figure 2
Output Characteristics ($T_J = 175^\circ\text{C}$)

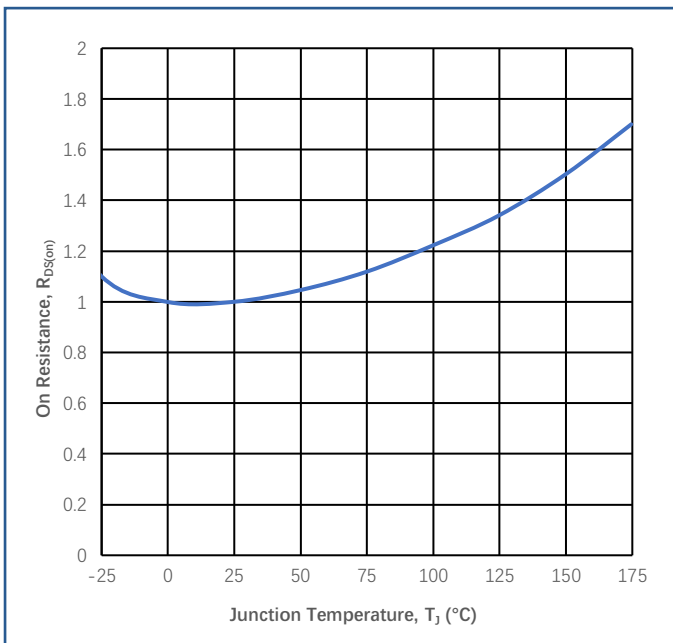


Figure 3
Normalized On-Resistance vs. Temperature

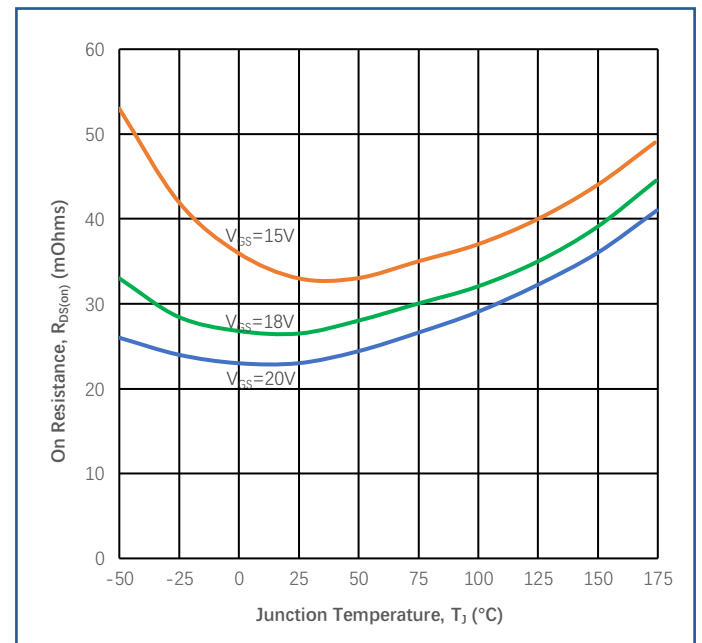


Figure 4
On-Resistance vs. Temperature

Typical Performance

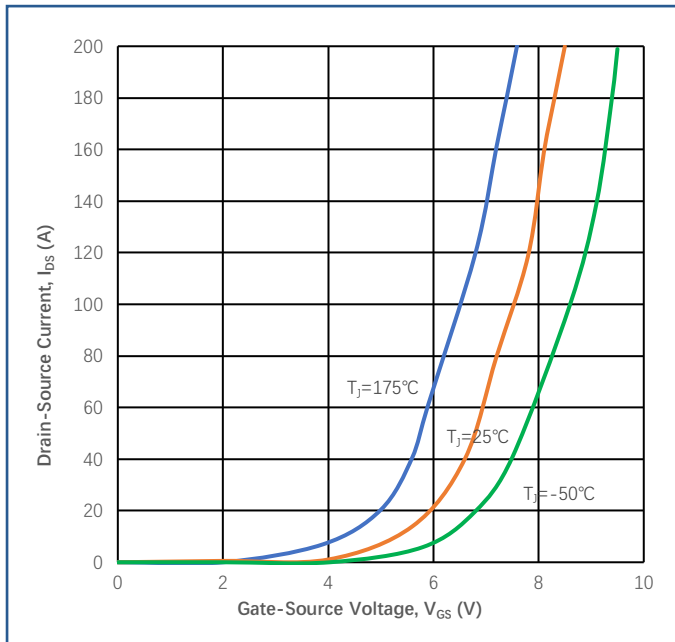


Figure 5
Transfer Characteristic

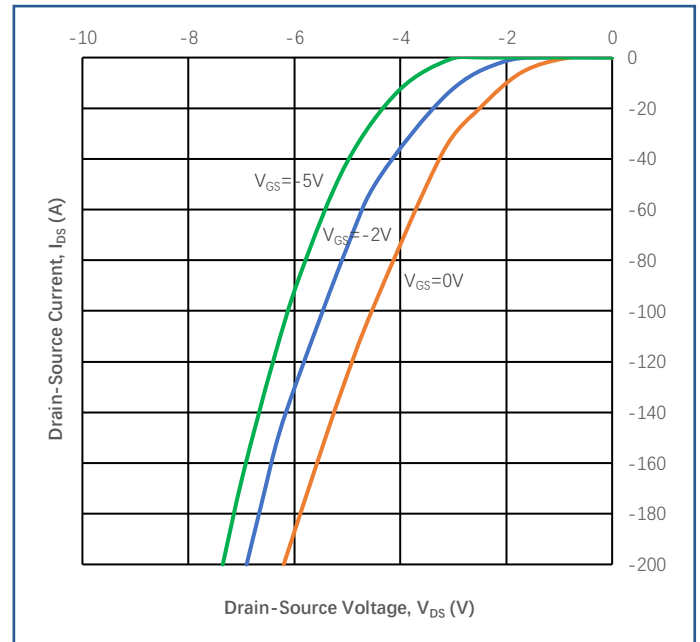


Figure 6
Body Diode Characteristic at 25°C

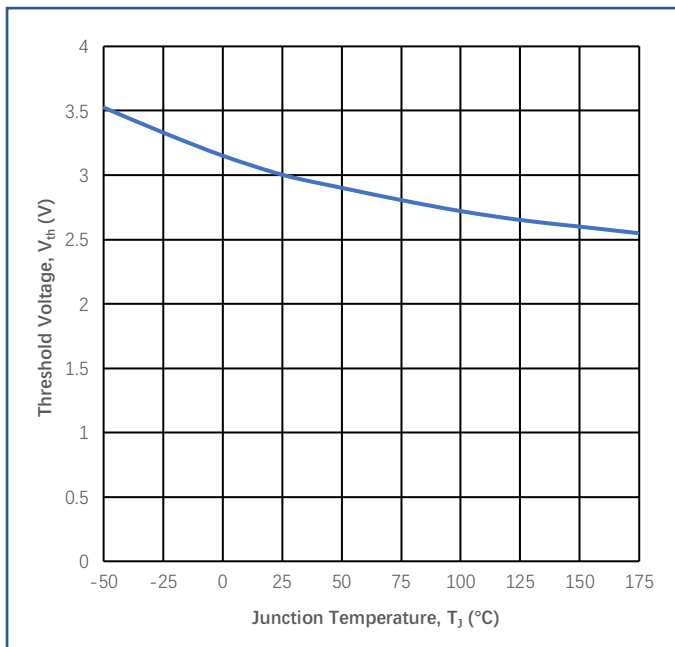


Figure 7
Threshold Voltage vs. Temperature

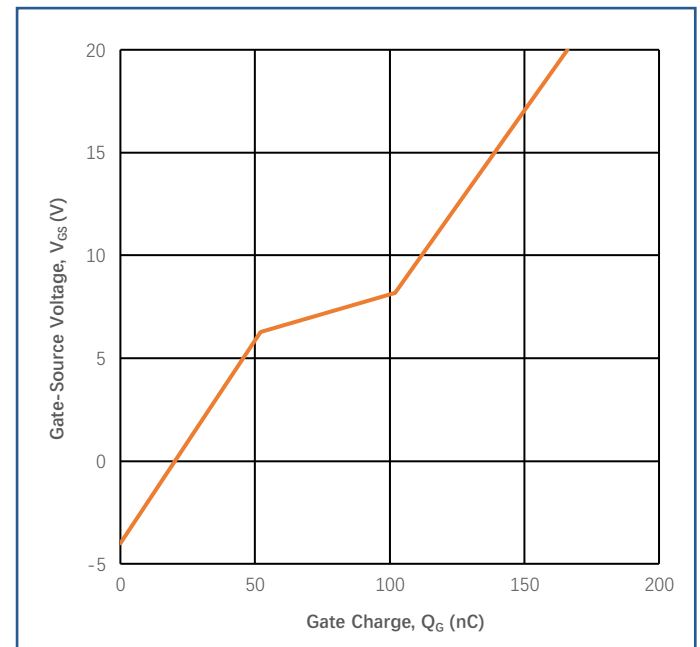


Figure 8
Gate Charge Characteristics

Typical Performance

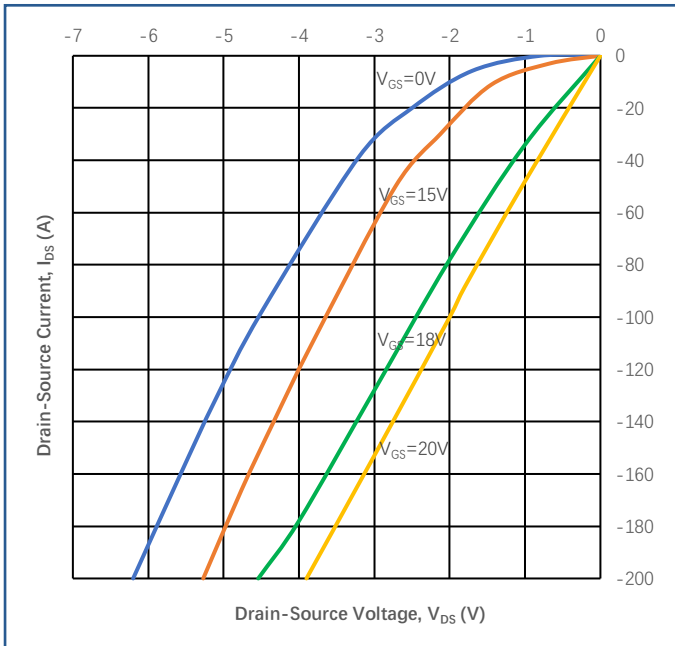


Figure 9
3rd Quadrant Characteristic at 25°C

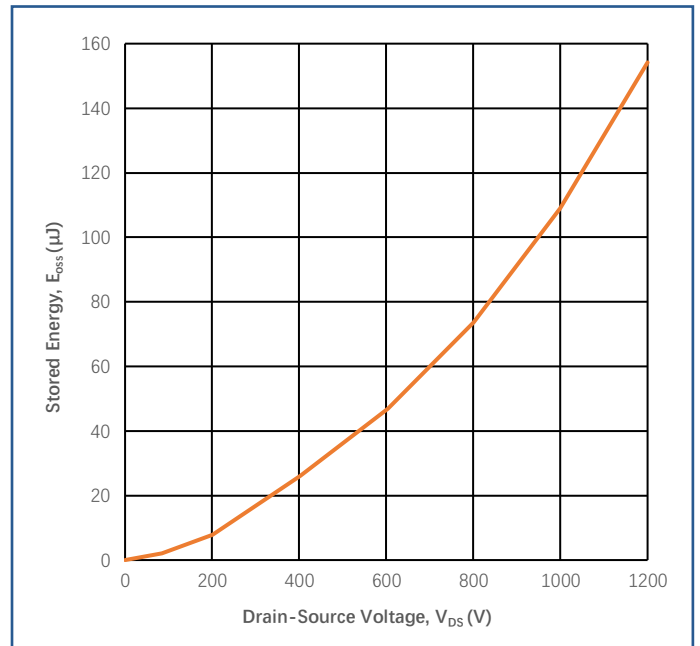


Figure 10
Output Capacitor Stored Energy

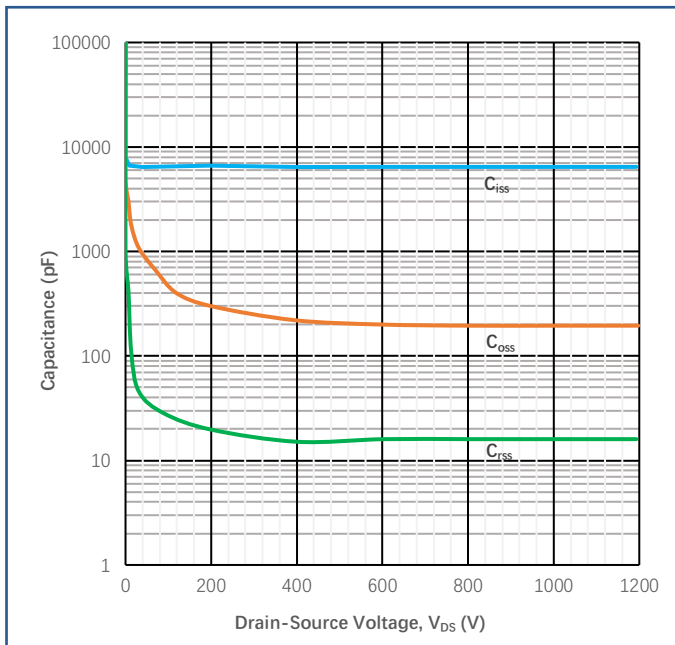


Figure 11
Capacitances vs. Drain-source

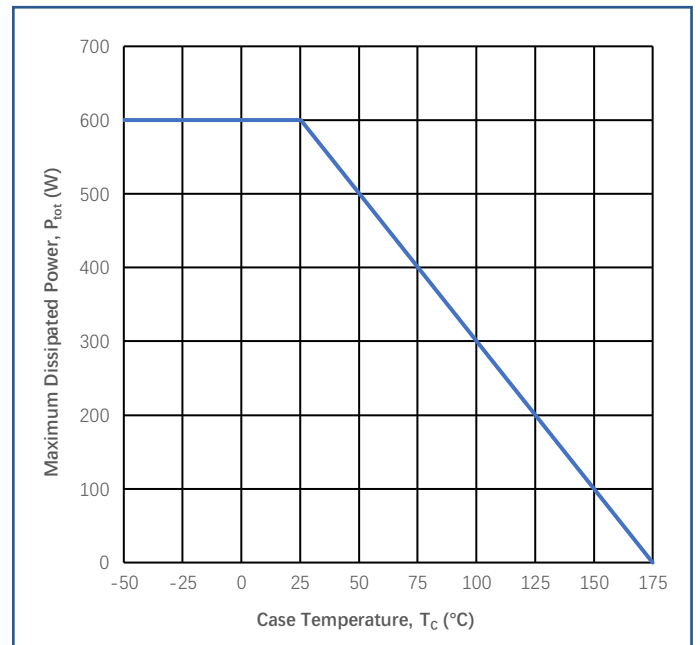


Figure 12
Max Power Dissipation Derating vs T_C

Typical Performance

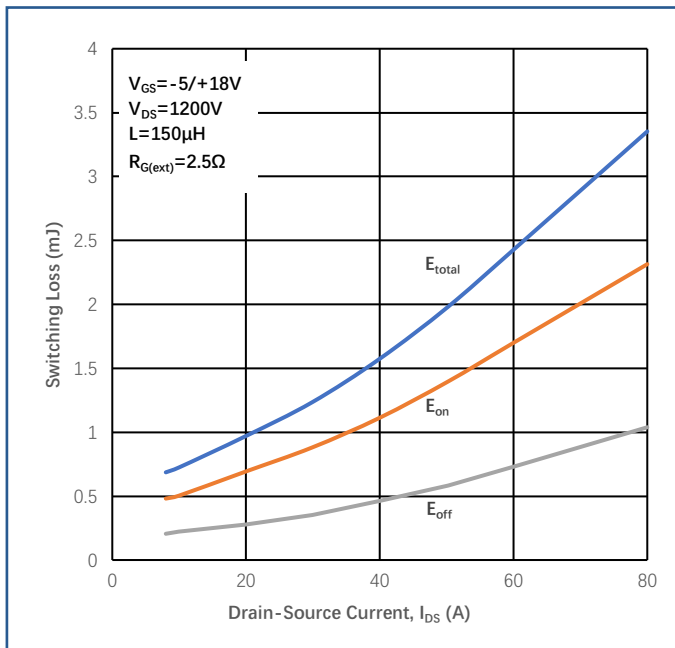


Figure 13

Switching Energy vs. Drain Current

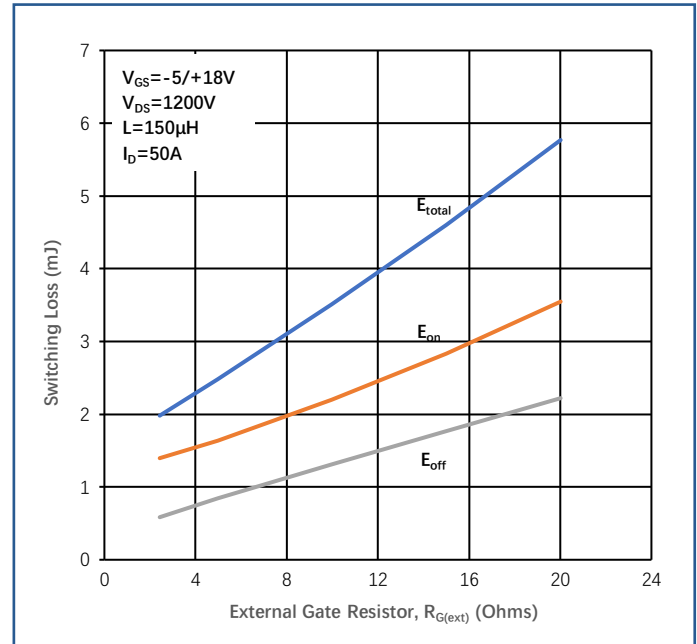


Figure 14

Switching Energy vs. $R_{G(ext)}$

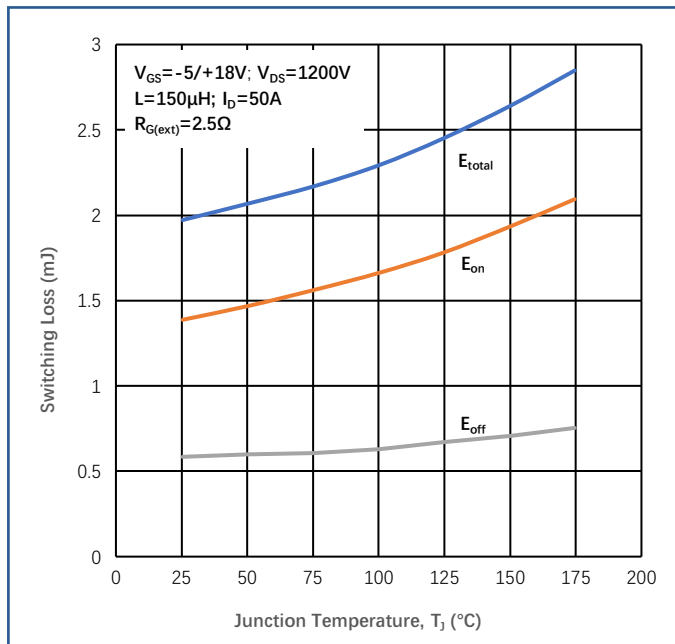


Figure 15

Switching Energy vs. Temperature

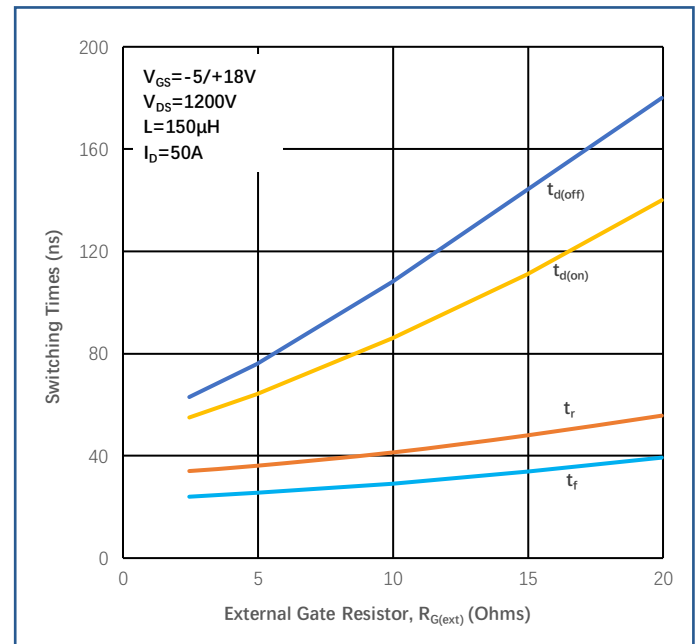


Figure 16

Switching Times vs. $R_{G(ext)}$

Typical Performance

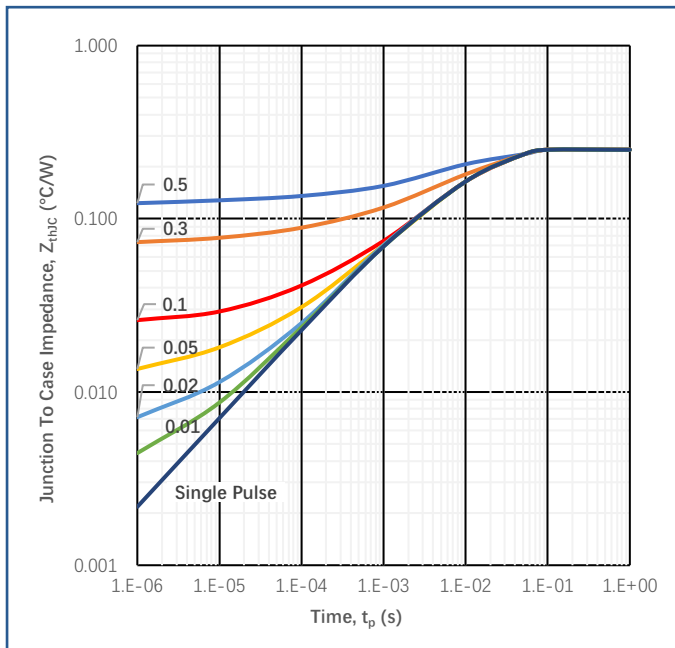


Figure 17
Transient Thermal Impedance

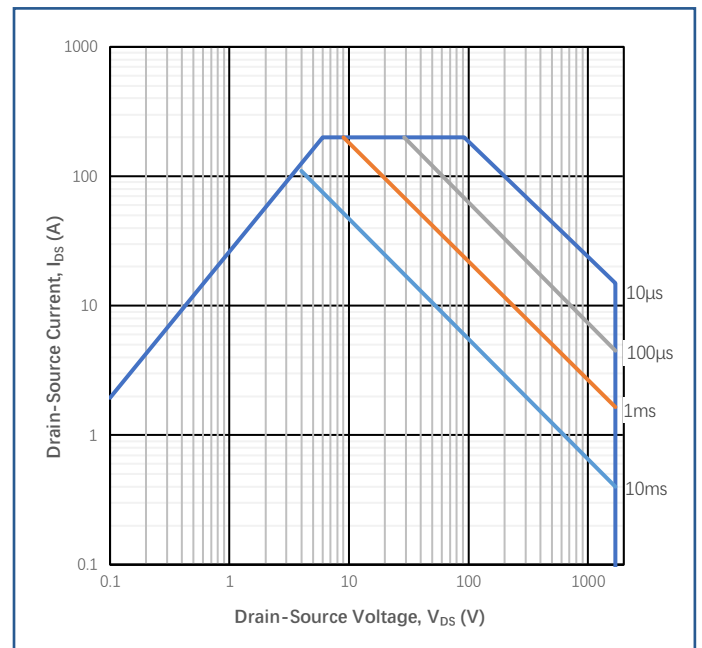
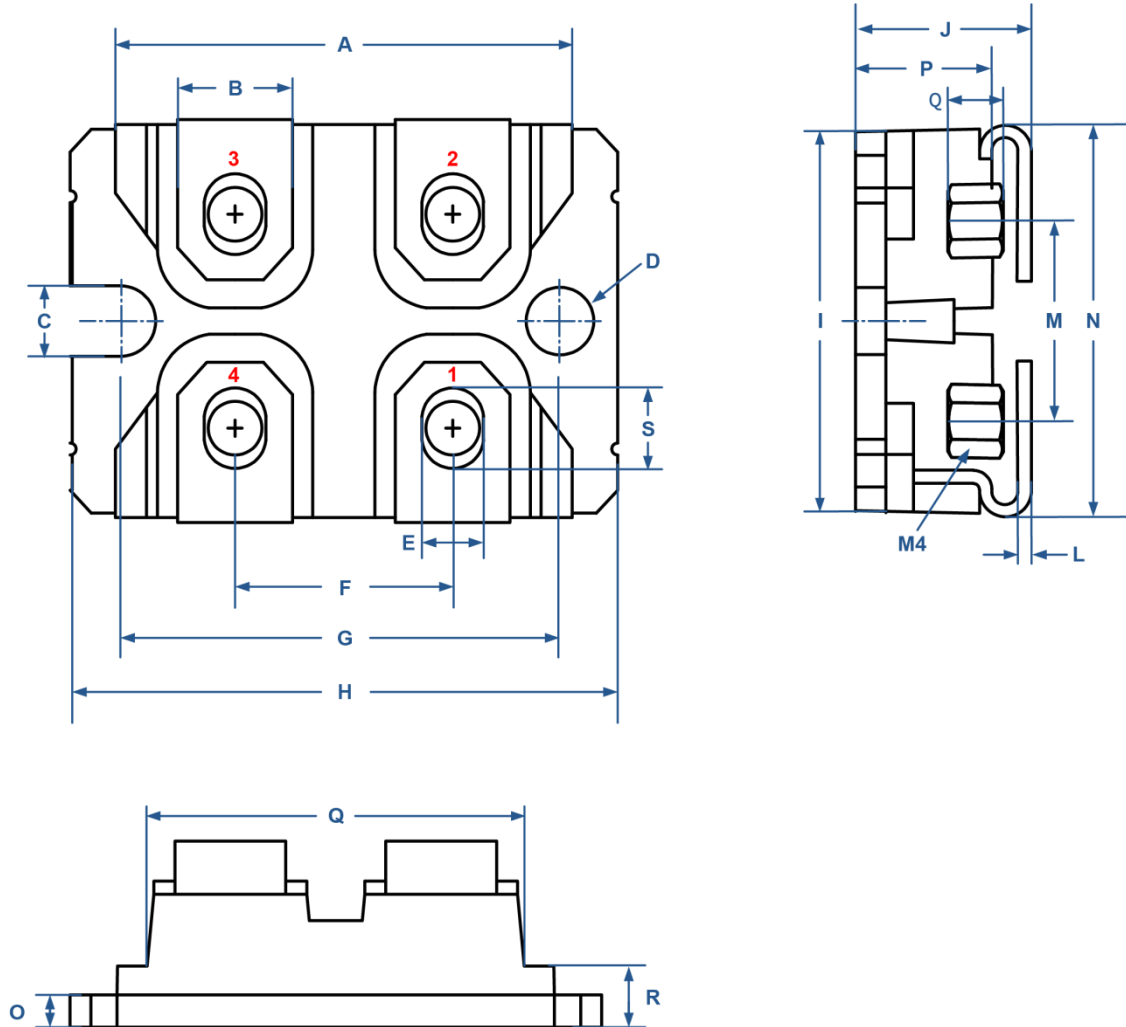


Figure 18
Safe Operating Area

Package Dimensions (mm)

Package Type: SOT-227



Symbol	Millimeters		Symbol	Millimeters	
	Min.	Max.		Min.	Max.
A	31.40	31.60	K *	9.40	9.60
B	7.70	8.10	L	0.75	0.85
C	4.20	4.40	M	12.40	12.80
D	4.20	4.40	N *	24.50	25.40
E	4.10	4.30	O *	1.90	2.10
F	14.90	15.10	P	3.10	3.95
G	30.10	30.40	Q *	26.60	27.00
H *	38.00	38.40	R *	3.80	4.20
I / T	23.80	24.20	S	5.10	5.40
J *	12.20	12.70	Mark * as main/key dimensions.		

Pin	Symbol	Description
1	S	Power Source
2	KS	Driver Source
3	G	Gate
4, Tab	D	Drain

Note:

1. All metal surfaces are Sn plated (matte), except area of cut.
2. Burr or mold flash size (0.5 mm) is not included in the dimensions.

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